Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application:

Listing of Claims:

1 (currently amended): A nitride light-emitting device having an adhesive reflecting layer comprising:

a metal reflecting layer having an upper surface and a lower surface;

a first reaction layer formed over the upper surface of the metal reflecting layer;

a transparent adhesive layer formed over the first reaction layer;

a second reaction layer formed over the transparent adhesive layer;

a nitride light-emitting stack layer formed over the second reaction layer, the nitride light-emitting stack layer comprising a first surface and a second surface;

a first electrode formed over the first surface; and

a second electrode formed over the second surface;

wherein each of the first and second reaction layers is formed to enhance an adhesion provided by the transparent adhesive layer.

2 (original): The nitride light-emitting device of claim 1 wherein the nitride light-emitting stack layer comprises a nitride first contact layer, the nitride first contact layer comprising a first surface and a second surface; a nitride first cladding layer formed over the first surface; a nitride light-emitting layer formed over the nitride first cladding layer; a nitride second cladding layer formed over the nitride light-emitting layer; and a nitride second contact layer formed over the nitride second cladding layer.

3 (original): The nitride light-emitting device of claim 2 wherein the first electrode is

formed over the second surface and the second electrode is formed over the nitride second contact layer.

4 (original): The nitride light-emitting device of claim 1 further comprising a first substrate formed over the lower surface of the metal reflecting layer.

5 (original): The nitride light-emitting device of claim 4 further comprising a metal heat sink formed over a lower surface of the first substrate.

6 (original): The nitride light-emitting device of claim 1 further comprising a metal heat sink formed over a lower surface of the metal reflecting layer.

7 (original): The nitride light-emitting device of claim 1 further comprising a second substrate formed between the second reaction layer and the light-emitting stack layer.

8 (original): The nitride light-emitting device of claim 1 further comprising a transparent conductive layer formed between the second reaction layer and the light-emitting stack layer.

9 (currently amended): The nitride light-emitting device of claim 8 wherein the transparent conductive layer ~~comprising~~ comprises a first surface and a second surface; the first electrode is formed over the first surface; the light-emitting stack layer is formed over the second surface; and the second electrode is formed over the light-emitting stack layer.

10 (currently amended): The nitride light-emitting device of claim 1 wherein the metal reflecting layer comprises at least one material selected from a material group

consisting of In, Sn, Al, Au, Pt, Zn, Ag, Pb, Pd, Ge, Cu, AuBe, AuGe, Ni, PbSn, and AuZn ~~, or other substitute materials~~.

11 (currently amended): The nitride light-emitting device of claim 1 wherein the first reaction layer comprises at least one material selected from a material group consisting of SiNx, Ti, and Cr ~~, or other substitute materials~~.

12 (currently amended): The nitride light-emitting device of claim 1 wherein the transparent adhesive layer comprises at least one material selected from a material group consisting of PI, BCB, and PFCB ~~, or other substitute materials~~.

13 (currently amended): The nitride light-emitting device of claim 1 wherein the second reaction layer comprises at least one material selected from a material group consisting of SiNx, Ti, and Cr ~~, or other substitute materials~~.

14 (currently amended): The nitride light-emitting device of claim 2 wherein the nitride first contact layer comprises at least one material selected from a material group consisting of GaN, InGaN, and AlGaN ~~, or other substitute materials~~.

15 (currently amended): The nitride light-emitting device of claim 2 wherein the nitride first cladding layer comprises at least one material selected from a material group consisting of AlN, GaN, AlGaN, InGaN, and AlInGaN ~~, or other substitute materials~~.

16 (currently amended): The nitride light-emitting device of claim 2 wherein the nitride light-emitting layer comprises at least one material selected from a material group consisting of GaN, InGaN, and AlInGaN ~~, or other substitute materials~~.

17 (currently amended): The nitride light-emitting device of claim 2 wherein the nitride

second cladding layer comprises at least one material selected from a material group consisting of AlNGaN, GaN, AlGaN, InGaN, and AlInGaN ~~, or other substitute materials~~.

18 (currently amended): The nitride light-emitting device of claim 2 wherein the nitride second contact layer comprises at least one material selected from a material group consisting of GaN, InGaN, and AlGaN ~~, or other substitute materials~~.

19 (currently amended): The nitride light-emitting device of claim 4 wherein the first substrate comprises at least one material selected from a material group consisting of silicon, GaAs, glass, quartz, GaP, GaAsP, AlGaAs, and metal ~~, or other substitute materials~~.

20 (currently amended): The nitride light-emitting device of claim 6 wherein the metal heat sink comprises at least one material selected from a material group consisting of Sn, Al, Au, Pt, Zn, Ag, Pb, Pd, Ge, Cu, AuBe, AuGe, Ni, PbSn, and AuZn ~~, or other substitute materials~~.

21 (currently amended): The nitride light-emitting device of claim 7 wherein the second substrate comprises at least one material selected from a material group consisting of Al_2O_3, SiC, ZnO, and GaN ~~, or other substitute materials~~.

22 (original): The nitride light-emitting device of claim 8 wherein the transparent conductive layer comprises at least one material selected from a material group consisting of indium tin oxide, cadmium tin oxide, antimony tin oxide, zinc oxide, and zinc tin oxide.

23 (new): The nitride light-emitting device of claim 13 wherein the transparent adhesive

layer comprises at least one material selected from a material group consisting of PI, BCB, and PFCB.

24 (new): The nitride light-emitting device of claim 12 wherein the first reaction layer comprises SiNx or Cr.

25 (new): The nitride light-emitting device of claim 11 wherein the transparent adhesive layer comprises PFCB.